

WAFER PROCESSING METHOD

ABSTRACT

A wafer processing method of processing a wafer having a device area where a plurality of devices are formed and a peripheral marginal area surrounding the device area on the front side of the wafer is disclosed. The devices are respectively formed in a plurality of separate regions defined by a plurality of division lines. Each device has a plurality of bump electrodes on the front side. The wafer processing method includes an annular modified layer forming step of applying a first laser beam through the dicing tape from the back side thereof along the boundary between the device area and the peripheral marginal area in the condition where the focal point of the first laser beam is set inside the wafer, thereby forming an annular modified layer inside the wafer along this boundary, and a modified layer forming step of applying a second laser beam through the dicing tape from the back side thereof along each division line in the condition where the focal point of the second laser beam is set inside the wafer, thereby forming a modified layer inside the wafer along each division line.

(Figure 6B)